

Title (en)
METHOD FOR DOPING SEMICONDUCTORS

Title (de)
VERFAHREN ZUM DOTIEREN VON HALBLEITERN

Title (fr)
PROCÉDÉ POUR DOPER DES SEMICONDUCTEURS

Publication
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Application
EP 15805391 A 20151201

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Abstract (en)
[origin: WO2016107662A1] The invention relates to a method for producing structured high-efficiency solar cells and photovoltaic elements that have differently doped regions. The invention also relates to the solar cells that are produced by said method and have increased efficiency.

IPC 8 full level
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